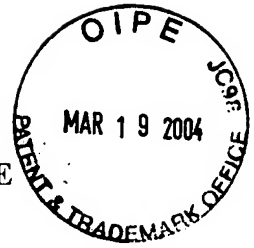


IN THE UNITED STATES PATENT AND TRADEMARK OFFICE



In re the Application of: **Shinichiroh IKEMASU, et al.**

Group Art Unit: **2814**

Serial No.: **10/050,169**

Examiner: **WEISS, Howard**

Filed: **January 18, 2002**

Confirmation No.: **9818**

For: **HIGHLY INTEGRATED AND RELIABLE DRAM AND ITS MANUFACTURE**

INFORMATION DISCLOSURE STATEMENT
PURSUANT TO 37 CFR 1.97(b)(4)

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

March 19, 2004

Sir:

The attention of the Patent and Trademark Office is hereby directed to the documents listed on the attached Form PTO-1449. The documents were made of record in related application Serial No. 10/166,620, filed June 12, 2002.

The above information is presented so that the Patent and Trademark Office can, in the first instance, determine any materiality thereof to the claimed invention. See 37 CFR 1.104(a) concerning the PTO duty to consider and use any such information. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the documents cited in the attached Form PTO-1449 be made of record therein and appear on the first page of any patent to issue therefrom.



The Commissioner is authorized to charge our Deposit Account No. 50-2866 for any fee which is deemed by the Patent and Trademark Office to be required to effect consideration of this statement.

Respectfully submitted,

WESTERMAN, HATTORI, DANIELS & ADRIAN, LLP

Stephen G. Adrian
Attorney for Applicant(s)
Reg. No. 32,878

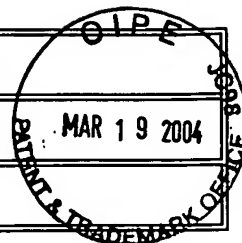
SGA/arf

Enclosures: PTO-1449 and 18 References

Attorney Docket No. **970607B**

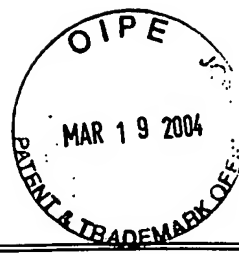
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| INFORMATION DISCLOSURE CITATION PTO-1449 | Atty. Docket No. 970607B | Serial No. 10/050,169 |
| | Applicant(s): Shinichiroh IKEMASU et al. | |
| | Filing Date: January 18, 2002 | Group Art Unit: 2814 |



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